

Amendments to the Claims

This listing of claims replaces all prior versions and listings of claims in the application.

Listing of Claims

1-9. (Canceled)

10. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion; [[and]]

a second wiring line formed over the first wiring line with an insulating film interposed therebetween,

wherein the first wiring line is formed on a same layer as a gate electrode of a thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other,
~~wherein a width of the first wiring line is smaller than a width of the second wiring line,~~
~~and the first and second wiring lines are arranged such that the second wiring line extends beyond opposite edges of the first wiring line, and~~

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and [[.]]

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

11. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 10, wherein the insulating film comprises an organic

resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

12. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 10, wherein the insulating film comprises silicon nitride.

13. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 10, wherein the insulating film comprises an interlayer insulating film.

14. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 10, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

15. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 10, wherein the second wiring line comprises aluminum.

16. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;

an insulating film formed over the first wiring line;

a second wiring line formed over the first wiring line with the insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed ~~between the third wiring line and the first and second portions of the first wiring line, and~~ between the third wiring line and the second wiring line,

wherein the first wiring line is formed on a same layer as a gate electrode of ~~[[the]]~~ a thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other, wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

17. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 16, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

18. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 16, wherein the insulating film comprises silicon nitride.

19. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 16, wherein the insulating film comprises an interlayer insulating film.

20. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 16, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

21. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 16, wherein the second wiring line comprises aluminum.

22. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;

an insulating film formed over the first wiring line;

a second wiring line formed over the first wiring line with the insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line; and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line,

wherein the insulating film is interposed ~~between the third wiring line and the first and second portions of the first wiring line, and~~ between the third wiring line and the second wiring line,

wherein the second wiring line is formed on a same layer as a source or a drain electrode of ~~[[the]]~~ a thin film transistor,

wherein the first wiring line and the second wiring line extend in parallel with each other,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

23. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 22, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

24. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 22, wherein the insulating film comprises silicon nitride.

25. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 22, wherein the insulating film comprises an interlayer insulating film.

26. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 22, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

27. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 22, wherein the second wiring line comprises aluminum.

28. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion; [[and]]

a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line, and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line,

wherein the insulating film is interposed between the third wiring line and the second wiring line,

wherein the first wiring line is formed on a same layer as a gate electrode of ~~the~~ a thin film transistor,

~~wherein a width of the first wiring line is smaller than that of the second wiring line, and the first and second wiring lines are arranged such that the second wiring line extends beyond opposite edges of the first wiring line,~~

~~wherein the first wiring line and the second wiring line extend in parallel with each other, and~~

wherein the second wiring line is along a lengthwise direction of the first wiring line,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and [[.]]

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

29. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 28, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

30. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 28, wherein the insulating film comprises silicon nitride.

31. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 28, wherein the insulating film comprises an interlayer insulating film.

32. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 28, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

33. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 28, wherein the second wiring line comprises aluminum.

34. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device comprising:

a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion; [[and]]

a second wiring line formed over the first wiring line with an insulating film interposed therebetween such that at least a portion of the second wiring line overlaps with the first wiring line, and

a third wiring line formed on a same surface as the first wiring line and extending between the first and second portions of the first wiring line and across the second wiring line, wherein the insulating film is interposed between the third wiring line and the second wiring line,

wherein one of the first wiring line and the second wiring line is formed on a same layer as a source or a drain electrode of ~~[[the]]~~ a thin film transistor,

~~wherein a width of the first wiring line is smaller than that of the second wiring line, and the first and second wiring lines are arranged such that the second wiring line extends beyond opposite edges of the first wiring line,~~

~~wherein the first wiring line and the second wiring line extend in parallel with each other, and~~

wherein the second wiring line is along a lengthwise direction of the first wiring line,

wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and

wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

35. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 34, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

36. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 34, wherein the insulating film comprises silicon nitride.

37. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 34, wherein the insulating film comprises an interlayer insulating film.

38. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 34, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

39. (Currently Amended) ~~An integrated circuit using a thin film transistor~~ A semiconductor device according to claim 34, wherein the second wiring line comprises aluminum.

40. (New) A semiconductor device comprising:
a first wiring line formed over a substrate, the first wiring line comprising at least a first portion and a second portion;
a second wiring line formed over the first wiring line with an insulating film interposed therebetween,
wherein one of the first wiring line and the second wiring line is formed on a same layer as a source or a drain electrode of a thin film transistor,
wherein the first wiring line and the second wiring line extend in parallel with each other,
wherein the first portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film, and
wherein the second portion of the first wiring line and the second wiring line are electrically connected with each other via a plurality of contact holes opened in the insulating film.

41. (New) A semiconductor device according to claim 40, wherein the insulating film comprises an organic resin film selected from the group consisting of polyimide, polyamide, polyimideamide, and acrylic.

42. (New) A semiconductor device according to claim 40, wherein the insulating film comprises silicon nitride.

43. (New) A semiconductor device according to claim 40, wherein the insulating film comprises an interlayer insulating film.

44. (New) A semiconductor device according to claim 40, wherein the first wiring line comprises at least one selected from the group consisting of aluminum, tantalum, polycrystalline silicon, and tungsten silicide.

45. (New) A semiconductor device according to claim 40, wherein the second wiring line comprises aluminum.

46. (New) A semiconductor device according to claim 10, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

47. (New) A semiconductor device according to claim 16, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

48. (New) A semiconductor device according to claim 22, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

49. (New) A semiconductor device according to claim 28, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

50. (New) A semiconductor device according to claim 34, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

51. (New) A semiconductor device according to claim 40, wherein the semiconductor device is a liquid crystal display device or an electroluminescence display device.

52. (New) A semiconductor device according to claim 10, wherein the insulating film comprises silicon oxide.

53. (New) A semiconductor device according to claim 16, wherein the insulating film comprises silicon oxide.

54. (New) A semiconductor device according to claim 22, wherein the insulating film comprises silicon oxide.

55. (New) A semiconductor device according to claim 28, wherein the insulating film comprises silicon oxide.

56. (New) A semiconductor device according to claim 34, wherein the insulating film comprises silicon oxide.

57. (New) A semiconductor device according to claim 40, wherein the insulating film comprises silicon oxide.

58. (New) A semiconductor device according to claim 10, wherein the insulating film is a laminate film.

59. (New) A semiconductor device according to claim 16, wherein the insulating film is a laminate film.

60. (New) A semiconductor device according to claim 22, wherein the insulating film is a laminate film.

61. (New) A semiconductor device according to claim 28, wherein the insulating film is a laminate film.

62. (New) A semiconductor device according to claim 34, wherein the insulating film is a laminate film.

63. (New) A semiconductor device according to claim 40, wherein the insulating film is a laminate film.